

# Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0032			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0039			
I <sub>D</sub> (A)	100			
Configuration	Single			

# D

#### **FEATURES**

- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- AEC-Q101 Qualifiedd
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



TO-252		Ŷ
G D S	Drain Connected to Tab	G
Top View		N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD100N03-3m2L-GE3

<b>ABSOLUTE MAXIMUM RATING</b>	S (T <sub>C</sub> = 25 °C, unles	s otherwise noted	(k		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	30	.,	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	1	100		
	T <sub>C</sub> = 125 °C	l <sub>D</sub>	89		
Continuous Source Current (Diode Conduct	I <sub>S</sub>	100	Α		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	150		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	60		
Single Pulse Avalanche Energy	L = U.1 MH	E <sub>AS</sub>	180	mJ	
Martin and Branch Branch and Branch	T <sub>C</sub> = 25 °C	D	136	10/	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	45	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	50	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	1.1	C/ VV

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		1.5	2.0	2.5		
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 30 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 125 °C	-	-	50	μA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 175 °C	-	-	150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.0027	0.0032		
Drain Cauras On State Besistance		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0049	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0058		
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 15 A	-	0.0031	0.0039		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		-	122	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	5053	6316	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 15 V, f = 1 MHz	-	921	1151		
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	377	471		
Total Gate Charge <sup>c</sup>	Qg			-	77	116	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 15 \text{ V}, I_{D} = 50 \text{ A}$	-	14.3	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	11	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.14	2.28	3.42	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD}$ = 15 V, $R_L$ = 0.3 $\Omega$ $I_D$ $\cong$ 50 A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		-	10	15		
Rise Time <sup>c</sup>	t <sub>r</sub>			-	10	15		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	42	63	ns -	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	10	15		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>	•			•			
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	150	А	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 40 A, V <sub>GS</sub> = 0 V			0.85	1.2	V	

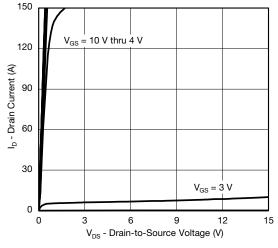
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

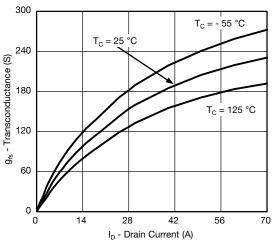
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



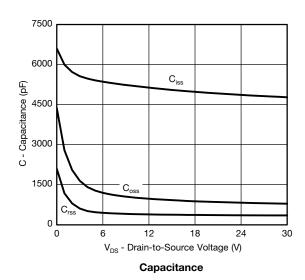
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

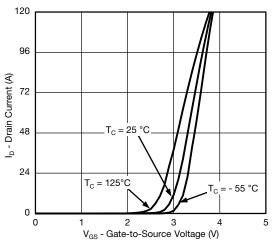


#### **Output Characteristics**

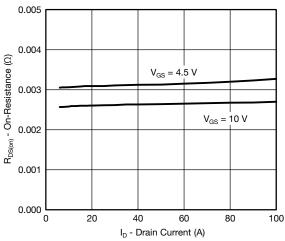


#### Transconductance

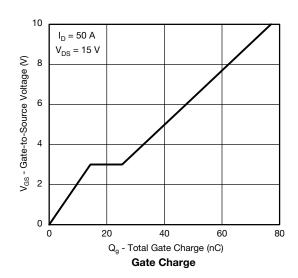




#### **Transfer Characteristics**

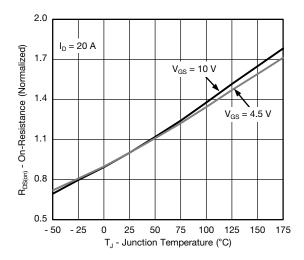


On-Resistance vs. Drain Current

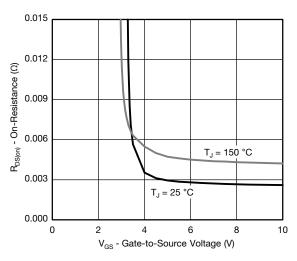




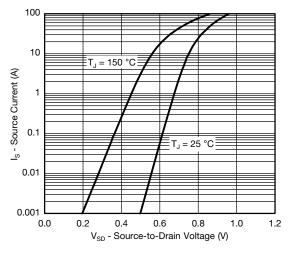
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



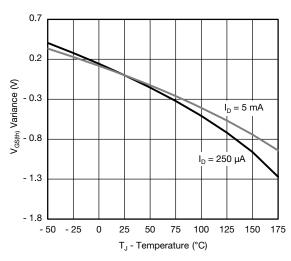
#### On-Resistance vs. Junction Temperature



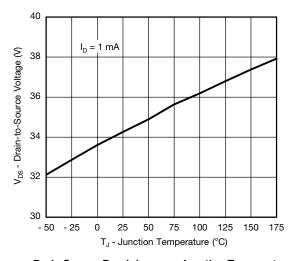
On-Resistance vs. Gate-to-Source Voltage



#### **Source Drain Diode Forward Voltage**



Threshold Voltage

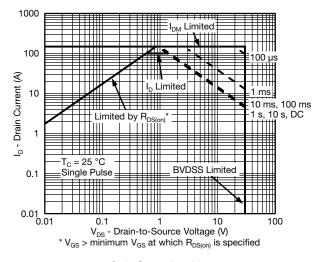


Drain Source Breakdown vs. Junction Temperature

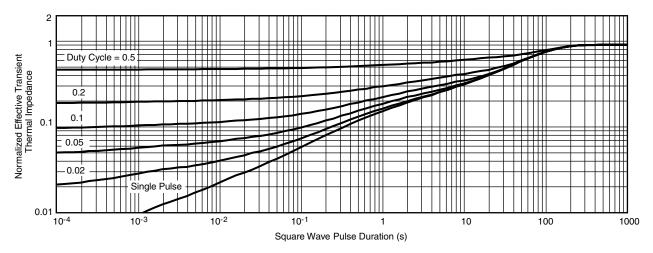
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## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



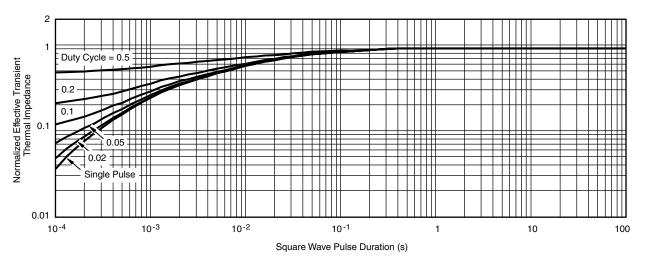
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

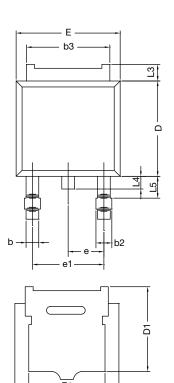
#### Note

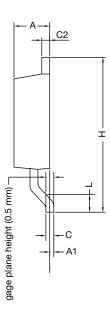
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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## **TO-252AA Case Outline**





	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56	BSC	0.180	BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13					

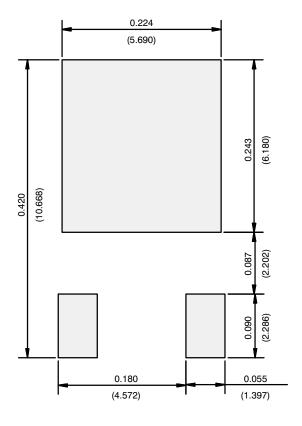
#### DWG: 6019

Note

• Dimension L3 is for reference only.



## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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